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(54) Title: WATERFALL WIRE BONDING

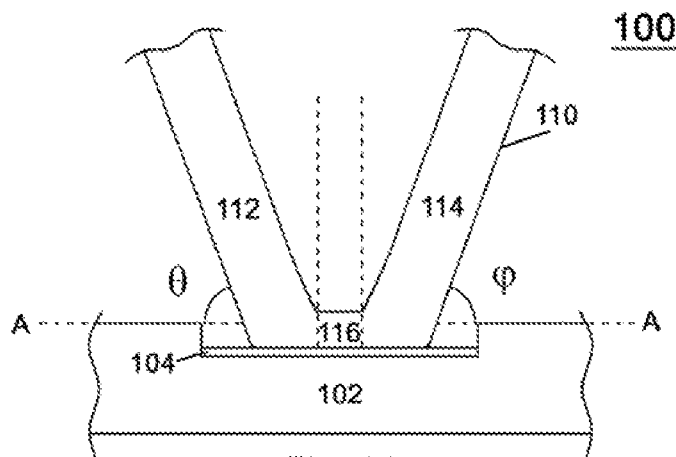


Fig. 1A

(57) Abstract: A wire bonded structure for a semiconductor device is disclosed. The wire bonded structure comprises a bonding pad; and a continuous length of wire mutually diffused with the bonding pad, the wire electrically coupling the bonding pad with a first electrical contact and a second electrical contact different from the first electrical contact.